

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J372R

#### 1. Applications

• Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 1.8-V gate drive voltage.
- (3) Low drain-source on-resistance

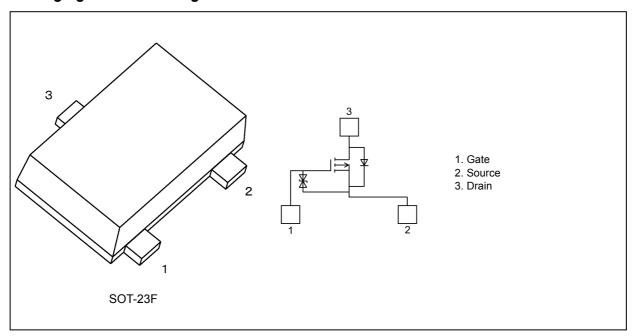
 $R_{\rm DS(ON)}$  = 144 m $\Omega$  (max) (@ $V_{\rm GS}$  = -1.8 V)

 $R_{DS(ON)} = 72.0 \text{ m}\Omega \text{ (max) (@V_{GS} = -2.5 V)}$ 

 $R_{\rm DS(ON)} = 50.0 \ {\rm m}\Omega \ ({\rm max}) \ ({\rm @V_{GS}} = -4.5 \ {\rm V})$ 

 $R_{\mathrm{DS(ON)}} = 42.0 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@V_{\mathrm{GS}} = -10 \ \mathrm{V})$ 

#### 3. Packaging and Pin Configuration



#### 4. Orderable part number

| Orderable part number | AEC-Q101 |          | Note           |          |  |  |
|-----------------------|----------|----------|----------------|----------|--|--|
| SSM3J372R,LF          | _        |          | General Use    |          |  |  |
| SSM3J372R,LXGF        | YES      | (Note 1) | Unintended Use | (Note 1) |  |  |
| SSM3J372R,LXHF        | YES      |          | Automotive Use |          |  |  |

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production



### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25°C)

| Characteristics        |            |            |                  | Rating     | Unit |
|------------------------|------------|------------|------------------|------------|------|
| Drain-source voltage   |            |            | V <sub>DSS</sub> | -30        | V    |
| Gate-source voltage    |            |            | V <sub>GSS</sub> | -12/+6     |      |
| Drain current (DC)     |            | (Note 1)   | I <sub>D</sub>   | -6.0       | Α    |
| Drain current (pulsed) |            | (Note 1,2) | I <sub>DP</sub>  | -24.0      |      |
| Power dissipation      |            | (Note 3)   | P <sub>D</sub>   | 1          | W    |
| Power dissipation      | (t < 10 s) | (Note 3)   | P <sub>D</sub>   | 2          | W    |
| Channel temperature    |            |            | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature    |            |            | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW)  $\leq$  1 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 6. Thermal Characteristics

| Characteristics                       |          | Symbol                | Max | Unit |
|---------------------------------------|----------|-----------------------|-----|------|
| Channel-to-ambient thermal resistance | (Note 1) | R <sub>th(ch-a)</sub> | 125 | °C/W |

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)



#### 7. Electrical Characteristics

#### 7.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                |          | Symbol               | Test Condition                                    | Min  | Тур. | Max  | Unit      |
|--------------------------------|----------|----------------------|---|------|------|------|-----------|
| Gate leakage current           |          | I <sub>GSS</sub>     | $V_{GS} = -10/+6 \text{ V}, V_{DS} = 0 \text{ V}$ | _    | _    | ±1   | μА        |
| Drain cut-off current          |          | I <sub>DSS</sub>     | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$    | _    | _    | -1   |           |
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | $I_D$ = -10 mA, $V_{GS}$ = 0 $V$                  | -30  | _    | _    | ٧         |
| Drain-source breakdown voltage | (Note 1) | V <sub>(BR)DSX</sub> | $I_D$ = -10 mA, $V_{GS}$ = 8 $V$                  | -22  | _    |      |           |
| Gate threshold voltage         | (Note 2) | $V_{th}$             | $V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$    | -0.5 | _    | -1.2 |           |
| Drain-source on-resistance     | (Note 3) | R <sub>DS(ON)</sub>  | $I_D = -5.0 \text{ A}, V_{GS} = -10 \text{ V}$    | _    | 36.0 | 42.0 | $m\Omega$ |
|                                |          |                      | $I_D = -4.0 \text{ A}, V_{GS} = -4.5 \text{ V}$   | _    | 42.5 | 50.0 |           |
|                                |          |                      | $I_D = -2.5 \text{ A}, V_{GS} = -2.5 \text{ V}$   | _    | 57.5 | 72.0 |           |
|                                |          |                      | I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.8 V | _    | 76.5 | 144  |           |
| Forward transfer admittance    | (Note 3) | Y <sub>fs</sub>      | $V_{DS} = -3 \text{ V}, I_D = -2.5 \text{ A}$     | 5.7  | 11.3 | _    | S         |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

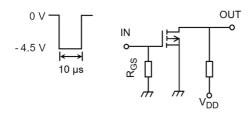
Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 7.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | $V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$                                      | _   | 560  | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | f = 1 MHz  | _   | 65   | _   |      |
| Output capacitance             | Coss             |  | 1   | 80   | _   |      |
| Switching time (turn-on time)  | t <sub>on</sub>  | $V_{DD}$ = -15 V, $I_{D}$ = -2.0 A<br>$V_{GS}$ = 0 to -4.5 V, $R_{GS}$ = 10 $\Omega$ | _   | 15   | _   | ns   |
| Switching time (turn-off time) | t <sub>off</sub> | Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns<br>Common source, See Chapter 7.3        |     | 75   |     |      |

#### 7.3. Switching Time Test Circuit



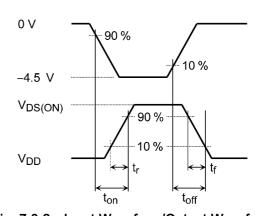


Fig. 7.3.1 Test Circuit of Switching Time

Fig. 7.3.2 Input Waveform/Output Waveform



## 7.4. Gate Charge Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition                                     | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | V <sub>DD</sub> = -15 V, V <sub>GS</sub> = -4.5 V, | _   | 8.2  | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> | $I_D = -6.0 \text{ A}$                             | _   | 1.1  | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 2.2  | _   |      |

# 7.5. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics       |          | Symbol    | Test Condition                                 | Min | Тур. | Max | Unit |
|-----------------------|----------|-----------|--|-----|------|-----|------|
| Diode forward voltage | (Note 1) | $V_{DSF}$ | I <sub>DR</sub> = 6.0 A, V <sub>GS</sub> = 0 V | _   | 0.90 | 1.2 | V    |

Note 1: Pulse measurement.

#### 8. Marking

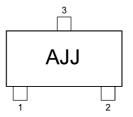


Fig. 8.1 Marking



#### 9. Characteristics Curves (Note)

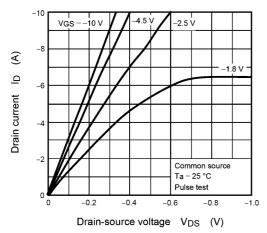


Fig. 9.1 I<sub>D</sub> - V<sub>DS</sub>

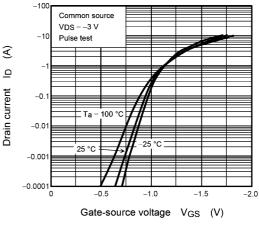


Fig. 9.2 I<sub>D</sub> - V<sub>GS</sub>

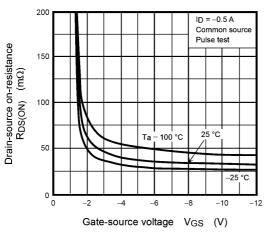


Fig. 9.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

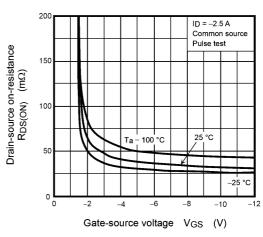


Fig. 9.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

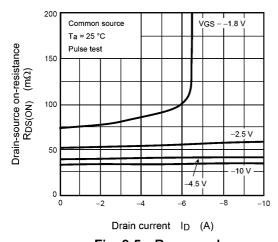


Fig. 9.5  $R_{DS(ON)}$  -  $I_D$ 

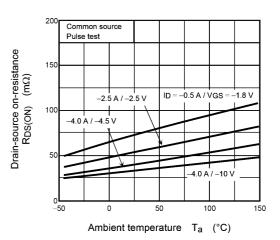


Fig. 9.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



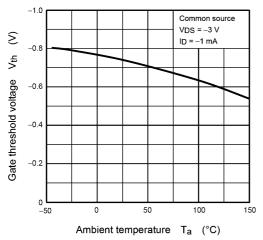


Fig. 9.7 V<sub>th</sub> - T<sub>a</sub>

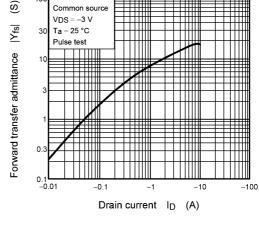


Fig. 9.8 |Y<sub>fs</sub>| - I<sub>D</sub>

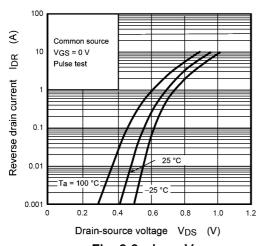


Fig. 9.9 I<sub>DR</sub> - V<sub>DS</sub>

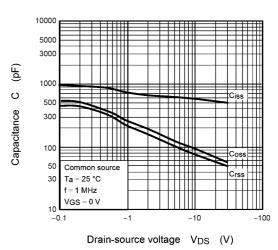


Fig. 9.10 C - V<sub>DS</sub>

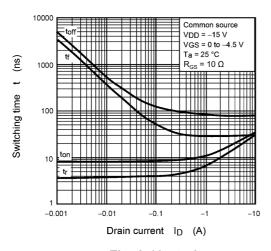


Fig. 9.11 t - I<sub>D</sub>

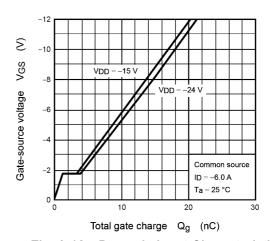


Fig. 9.12 Dynamic Input Characteristics



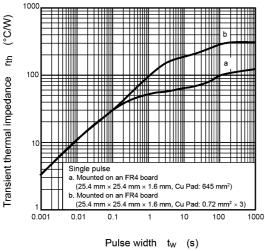
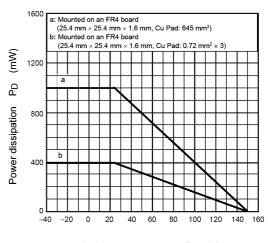


Fig. 9.13 r<sub>th</sub> - t<sub>w</sub>



Ambient temperature  $T_a$  (°C) Fig. 9.14  $P_D - T_a$ 

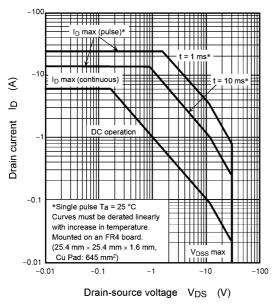


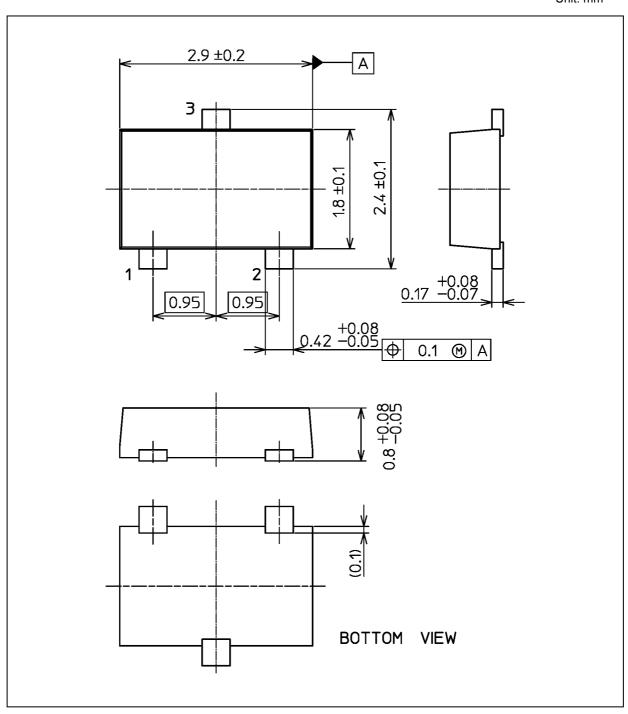
Fig. 9.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)
Nickname: SOT-23F

Rev.6.0



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